YJ Planar Schottky Barrier Diode Die Specification

45V 25A, 130mil, Schottky barrier diode die based on silicon planar process Part No.: PSB130M045SS-290A

Main Products Characterstics

- Average forward current: IF(AV) = 25 A
- Maximum operating junction temperature: Tj = 150 °C
- ESD rating: >15KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag



Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V _{RRM}	45 V
Average forward current	I _{F(AV)}	25 A
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	320 A
Storage temperature range	T _{stg}	-50 to +150 °C
Maximum operating junction temperature	Tj	150 °C

Static Electrical Characteristics (Ta = 25°C)					
Parameter	Symbol	Value			
Faranieter		Spec	Typical		
Reverse breakdown voltage I _R = 1mA	V_{BR}	50 V	54V		
Maximum forward voltage drop					
I _F = 25 A	V _F	0.55V	0.52V		
Pulse Test: tp = 300 $\mu s, \delta \leqslant 2\%$					
Maximum reverse current					
$V_{R} = V_{RRM}$	I _R	150uA	90uA		
Pulse Test: tp = 300 μ s, $\delta \le 2\%$					

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled. Yangjie Electronics does not guarantee device performance after assembly.	Recommended Storage Environment: Store in original container, in dessicated nitrogen, with no contamination.
All operating parameters must be validated for each customer application by customer's technical experts.	
Data sheet information is subjected to change without notice.	If the storage is done in normal atmosphere shelf life is reduced to 6 months.

扬州扬杰电子科技股份有限公司	电话: 0514-80982389
Yangzhou Yangjie Electronics Technology Co.,Ltd.	传真: 0514-80980189

Yangzhou Yangjie Electronics Technology Co., Ltd.

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